This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claim 1 (Currently amended): A semiconductor with integrated monitoring comprising:

a first light emitting semiconductor device formed on a predetermined substrate;

a passivation layer formed on top of a portion of said first semiconductor device, wherein the remaining portion of said semiconductor device not covered by said passivation layer [including] forms a window; and

a light monitoring device formed on top of said [passivation layer] window for monitoring leakage light from said first semiconductor device through said window.

Claim 2 (Original): The semiconductor as recited in claim 1, wherein said first semiconductor device is an active device.

Claim 3 (Previously presented): The semiconductor as recited in claim 1, wherein said predetermined substrate is a GaAs substrate.

Claim 4 (Previously presented): The semiconductor as recited in claim 1, wherein said predetermined substrate is a InP substrate.

Claim 5 (Previously presented): The semiconductor as recited in claim 1, wherein said predetermined substrate is a GaN substrate.

Claim 6 (Cancelled)

Claim 7 (Original): The semiconductor as recited in claim 1, wherein said first semiconductor device is a light emitting device.

Claim 8 (Original): The semiconductor as recited in claim 6, wherein said light emitting device is a laser.

Claim 9 (Original): The semiconductor as recited in claim 8, wherein said laser is a vertical cavity surface emitting laser (VCSEL).

Claim 10 (Cancelled)

Claim 11 (Original): The semiconductor as recited in claim 1, wherein said monitoring device is a light receiving device.

Claim 12 (Original): The semiconductor as recited in claim 10, wherein said light transmitting device is a photodiode.

Claim 13 (Original): The semiconductor as recited in claim 11, wherein said light receiving device is a photodetector.

Claims 14-22 (Cancelled)